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2SD2679

Transistors

# 2A / 30V Bipolar transistor

## 2SD2679

●Applications

Low frequency amplification, driver

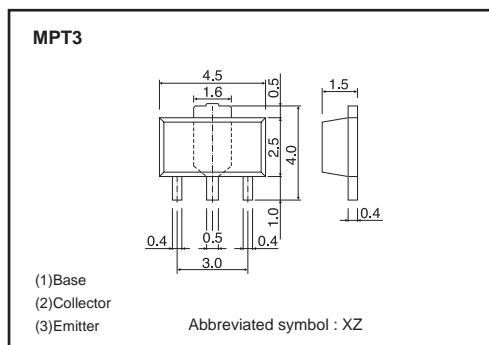
●Features

- 1) Collector current is high.
- 2) Low collector-emitter saturation voltage.  
 $(V_{CE(sat)} \leq 350\text{mV at } I_c = 1.5\text{A, } I_b = 75\text{mA})$

●Structure

NPN epitaxial planar silicon transistor

●Dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CBO}$	30	V
Collector-emitter voltage	$V_{CEO}$	30	V
Emitter-base voltage	$V_{EBO}$	6	V
Collector current	DC	2	A
	Pulse	4 *1	
Power dissipation	$P_C$	0.5 *2	W
		2 *3	
Junction temperature	$t_j$	150	°C
Storage temperature	$t_{stg}$	-55 to +150	°C

\*1  $P_w=1\text{ms}$ , single pulse.  
 \*2 Each terminal mounted on a recommended land.  
 \*3 Mounted on a 40x40x0.7mm ceramic board.

●Packaging specifications

Part No.	Package	MPT3
2SD2679	Package type	Taping
	Code	T100
	Basic ordering unit (pieces)	1000

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	$BV_{CEO}$	30	-	-	V	$I_c=1\text{mA}$
Collector-base breakdown voltage	$BV_{CBO}$	30	-	-		$I_c=10\mu\text{A}$
Emitter-base breakdown voltage	$BV_{EBO}$	6	-	-		$I_E=10\mu\text{A}$
Collector cut-off current	$I_{CBO}$	-	-	100	nA	$V_{CB}=30\text{V}$
Emitter cut-off current	$I_{EBO}$	-	-	100		$V_{EB}=6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$ *	-	180	370	mV	$I_c/I_b=1.5\text{A}/75\text{mA}$
DC current gain	$h_{FE}$	270	-	680	-	$V_{CE}=2\text{V, } I_c=200\text{mA}$
Transition frequency	$f_T$	-	280	-	MHz	$V_{CE}=2\text{V, } I_E=-200\text{mA, } f=100\text{MHz}$
Collector output capacitance	$C_{ob}$	-	20	-	pF	$V_{CB}=10\text{V, } I_E=0\text{mA, } f=1\text{MHz}$

\* Pulsed

Transistors

●Electrical characteristics curves

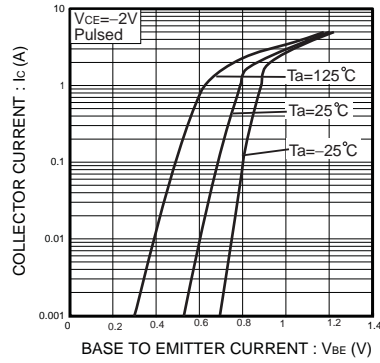


Fig.1 Grounded emitter propagation characteristics

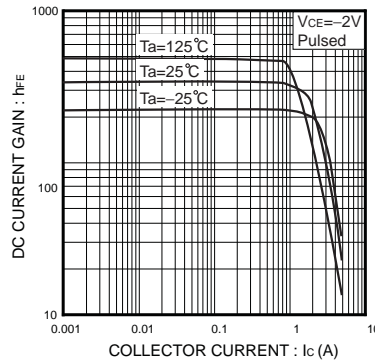


Fig.2 DC current gain vs. collector current

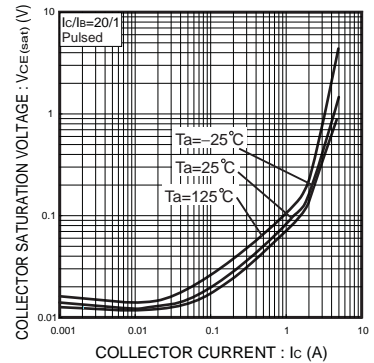


Fig.3 Collector-emitter saturation voltage base-emitter saturation voltage vs. collector current

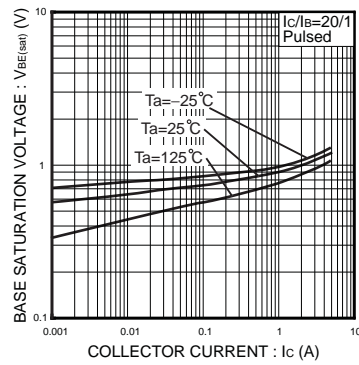


Fig.4 Base-emitter saturation voltage vs. collector current

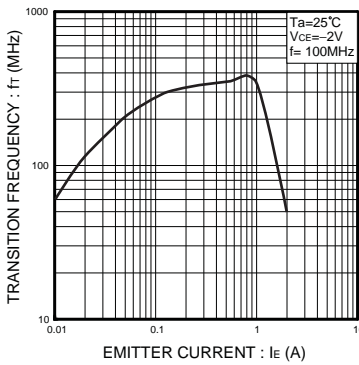


Fig.5 Gain bandwidth product vs. emitter current

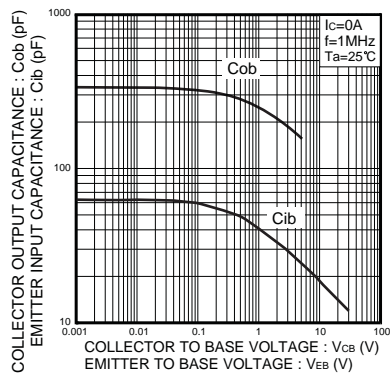


Fig.6 Collector output capacitance vs. collector-base voltage  
 Emitter input capacitance vs. emitter-base voltage

## Appendix

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